

ABSTRACT

An object of the present invention is to suppress a layer-peeling phenomenon in a semiconductor device comprising at least a ferroelectric layer and an upper electrode formed thereon while maintaining the electrical properties of the ferroelectric layer. The semiconductor device of the present invention is characterized in that an upper electrode and a ferroelectric layer have a convex region. By this constitution, a layer peeling can be suppressed. In the present invention, one convex region is formed on one layer, but a plurality of convex regions may be formed on one layer. Alternatively, a concave region may be formed in place of the convex region.

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